

## BD376/378/380

# Medium Power Linear and Switching Applications

Complement to BD375, BD377 and BD379 respectively



## **PNP Epitaxial Silicon Transistor**

1. Emitter 2.Collector 3.Base

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CBO}$	Collector-Base Voltage : BD376	- 50	V	
	: BD378	- 75	V	
	: BD380	- 100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage : BD376	- 45	V	
	: BD378	- 60	V	
	: BD380	- 80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V	
I <sub>C</sub>	Collector Current (DC)	- 2	Α	
I <sub>CP</sub>	*Collector Current (Pulse)	- 3	Α	
I <sub>B</sub>	Base Current	- 1	Α	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	25	W	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C	

## **Electrical Characteristics** $T_C=25\,^{\circ}\text{C}$ unless otherwise noted

Symbol	Paramete	er	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)		ng Voltage BD376 BD378 BD380	I <sub>C</sub> = - 100mA, I <sub>B</sub> = 0	- 45 - 60 - 80			V V V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	: BD376 : BD378 : BD380	$I_C = -100\mu A, I_E = 0$	- 50 - 75 - 100			V V V
I <sub>CBO</sub>		: BD376 : BD378 : BD380	$V_{CB} = -45V, I_{E} = 0$ $V_{CB} = -60V, I_{E} = 0$ $V_{CB} = -80V, I_{E} = 0$			- 2 - 2 - 2	μΑ μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = -5V, I_{C} = 0$			- 100	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	*DC Current Gain		V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 0.15A V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 1A	40 20		375	
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation	n Voltage	I <sub>C</sub> = - 1A, I <sub>B</sub> = - 0.1A			- 1	V
V <sub>BE</sub> (on)	*Base-Emitter ON Voltage		$V_{CE} = -2V, I_{C} = -1A$			- 1.5	V
t <sub>ON</sub>	Turn ON Time		$V_{CC} = -30V, I_{C} = -0.5A$		50		ns
t <sub>OFF</sub>	Turn OFF Time		$I_{B1} = -I_{B2} = -0.05A$ $R_{L} = 60\Omega$		500		ns

<sup>\*</sup> Pulse Test: PW=350μs, duty Cycle=2% Pulsed

## **h**<sub>FE</sub> Classification

Classification	6	10	16	25
h <sub>FE1</sub>	40 ~ 100	63 ~ 160	100 ~ 250	150 ~ 375

## **Typical Characteristics**

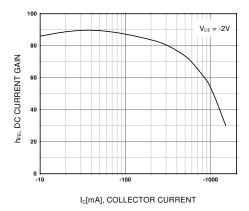


Figure 1. DC current Gain

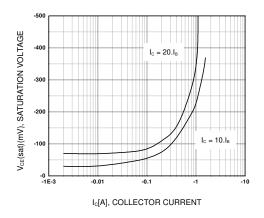


Figure 2. Collector-Emitter Saturation Voltage

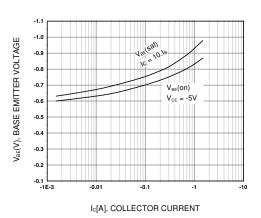


Figure 3. Base-Emitter Voltage

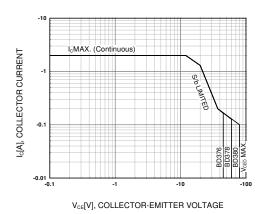


Figure 4. Safe Operating Area

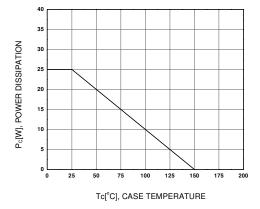


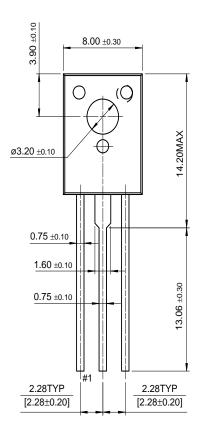
Figure 5. Power Derating

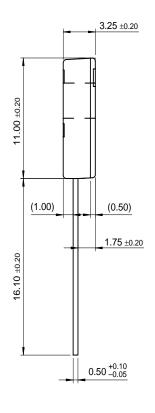
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BD376/378/380

## **Package Demensions**

TO-126





Dimensions in Millimeters

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